



#### **DUAL P-CHANNEL ENHANCEMENT MODE MOSFET**

## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
-20V	$75m\Omega @ V_{GS} = -4.5V$	-3.8A
-207	$137m\Omega @ V_{GS} = -2.5V$	-3.0A

## Description

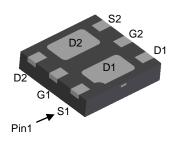
This MOSFET is designed to minimize on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## **Applications**

- Load Switch
- Power Management Functions
- Portable Power Adaptors

U-DFN2020-6 (Type B)





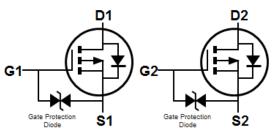
**Bottom View** 

### **Features**

- Low On-Resistance
- Low Input Capacitance
- Low Profile, 0.6mm Max Height
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

### **Mechanical Data**

- Case: U-DFN2020-6 (Type B)
- Case Material: Molded Plastic, "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202. Method 208 <sup>64</sup>
- Terminals Connections: See Diagram Below
- Weight: 0.0065 grams (Approximate)



Q1 P-CHANNEL MOSFET

Q2 P-CHANNEL MOSFET

Internal Schematic

## Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2075UFDB -7	U-DFN2020-6 (Type B)	3,000/Tape & Reel
DMP2075UFDB -13	U-DFN2020-6 (Type B)	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

# **Marking Information**

U-DFN2020-6 (Type B)



O3 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: E = 2017) M = Month (ex: 9 = September)

Date Code Key

Year	2017	2018	20	019	2020	2021		2022	2023	202	24	2025
Code	E	F		G	Н	1		J	K	L		М
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# **Maximum Ratings** (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	-20	V
Gate-Source Voltage	V <sub>GSS</sub>	±8	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = 4.5V	ID	-3.8 -3.0	А
Maximum Continuous Body Diode Forward Current (Note 5)	I <sub>S</sub>	-1.0	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	-25	Α
Avalanche Current (Note 7) L = 0.1mH	I <sub>AS</sub>	-13	Α
Avalanche Energy (Note 7) L = 0.1mH	E <sub>AS</sub>	8.5	mJ

## **Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	$P_{D}$	0.7	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	178	°C/W
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	P <sub>D</sub>	1.4	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	92	°C/W	
Thermal Resistance, Junction to Case (Note 6)	R <sub>0JC</sub>	22	*C/vv	
Operating and Storage Temperature Range		$T_{J_i}T_{STG}$	-55 to +150	°C

## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

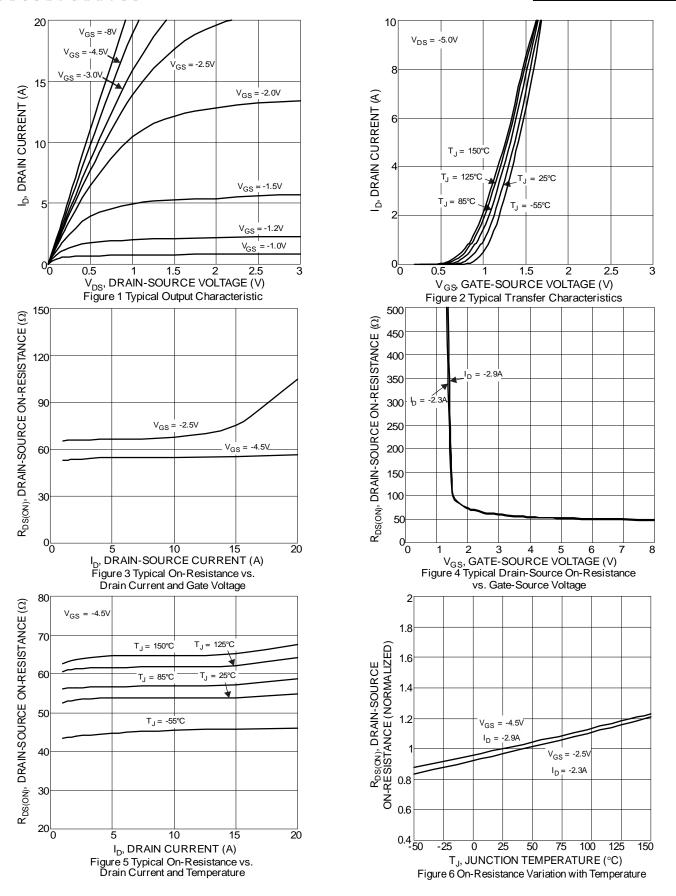
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)			•	•	•	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	_	_	-1.0	μA	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±10	μA	$V_{GS} = \pm 8V$ , $V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-0.35	_	-1.4	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$
Static Drain-Source On-Resistance		_	53	75	mΩ	$V_{GS} = -4.5V$ , $I_D = -2.9A$
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	64	137	11122	$V_{GS} = -2.5V, I_D = -2.3A$
Diode Forward Voltage	V <sub>SD</sub>	_	-0.7	-1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -3.0A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C <sub>ISS</sub>		642	_	pF	101/11/
Output Capacitance	Coss	_	98	_	pF	$V_{DS} = -10V, V_{GS} = 0V,$ f = 1.0MHz
Reverse Transfer Capacitance	C <sub>RSS</sub>	_	87	_	pF	1 - 1.00012
Gate Resistance	Rg	_	26.5	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$
Total Gate Charge (V <sub>GS</sub> = -4.5V)			8.8	_	nC	
Total Gate Charge (V <sub>GS</sub> = -8V)	Qg	_	0.9	_	nC	101/ 1 274
Gate-Source Charge	Qgs	_	2.9	_	nC	$V_{DS} = -10V, I_D = -3.7A$
Gate-Drain Charge	$Q_{gd}$	_	5.5	_	nC	]
Turn-On Delay Time	t <sub>D(ON)</sub>	_	22.6	_	ns	
Turn-On Rise Time	t <sub>R</sub>	_	34.1	_	ns	$V_{DD} = -10V, V_{GS} = -4.5V,$
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	34.3	_	ns	$R_L = 3.3\Omega, R_g = 1\Omega$
Turn-Off Fall Time	t <sub>F</sub>	_	13	_	ns	1
Body Diode Reverse Recovery Time	t <sub>RR</sub>	_	3.3	_	ns	$I_S = -3.0A$ , $dI/dt = 100A/\mu s$
Body Diode Reverse Recovery Charge	$Q_{RR}$	_	642	_	nC	I <sub>S</sub> = -3.0A, dI/dt = 100A/µs

Notes: 5. Device mounted on on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.

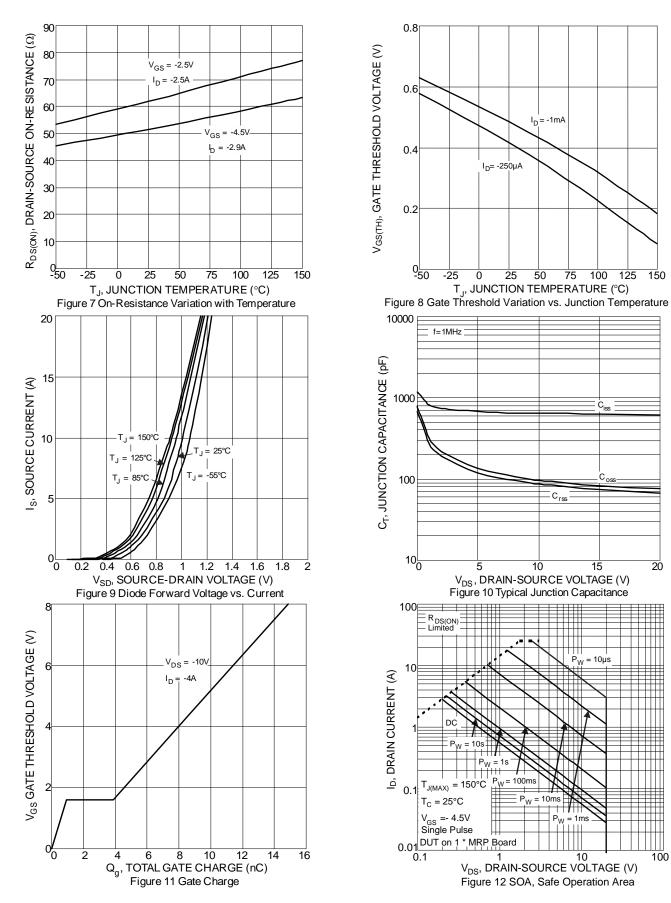
- 6. Short duration pulse test used to minimize self-heating effect
- 7. I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
  8. Short duration pulse test used to minimize self-heating effect.
  9. Guaranteed by design. Not subject to product testing.











100

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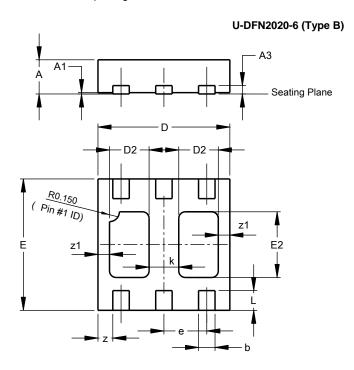






## **Package Outline Dimensions**

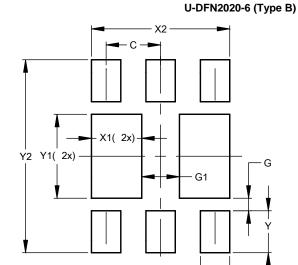
Please see http://www.diodes.com/package-outlines.html for the latest version.



U-DFN2020-6 Type B								
Dim	Min							
Α	0.545	0.605	0.575					
A1	0.00	0.05	0.02					
A3	-	-	0.13					
b	0.20	0.30	0.25					
D	1.95	2.075	2.00					
D2	0.50	0.70	0.60					
е	-	-	0.65					
E	1.95	2.075	2.00					
E2	0.90	1.10	1.00					
k	-	-	0.45					
L	0.25	0.35	0.30					
Z	-	-	0.225					
z1	-	-	0.175					
All Dimensions in mm								

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value			
	(in mm)			
С	0.650			
G	0.150			
G1	0.450			
X	0.350			
X1	0.600			
X2	1.650			
Y	0.500			
Y1	1.000			
Y2	2.300			



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